

ABSTRACT

An electrostatic discharge (ESD) protective structure is configured and arranged to protect an integrated semiconductor circuit that is located between a first potential bus with a first supply potential and a second potential bus with a second supply potential. The ESD protective structure includes a laterally shaped ESD diode having a first region with a first conduction type and a second region of a second conduction type spaced apart from the first region. The ESD protective structure is located between the potential busses and is provided with a gate electrode, such that the first region and the second region are adjusted with respect to the gate electrode, and the spacing between the first region and the second region corresponds to the length of the gate electrode.

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